See detailed ordering and shipping information on page 6 of this data sheet.

**ORDERING INFORMATION** 

# NGTB10N60FG

# **N-Channel IGBT** 600V, 10A, VCE(sat);1.5V, TO-220F-3FS

#### 主要特长

- IGBT VCE (sat)=1.5V typ. (IC=10A, VGE=15V) Diode VF=1.3V typ.(IF=10A)
- IGBT I<sub>C</sub>=20A (Tc=25°C)
- 适应全绝缘型封装
- 5µs抗短路能力

#### 应用

- 白物家电的功率因数校正
- 通用变频器 (General purpose inverter)

#### 规格

绝对最大额定值 / Ta = 25℃ (除非特殊指定)

参数	记号	条件		值	单位
Collector-Emitter 电压	VCES			600	V
Gate-Emitter 电压	VGES			±20	V
Collector 电流 (DC)	IC*1	受限于 Tjmax	@ Tc=25°C * <sup>2</sup>	20	А
			@ Tc=100°C *2	10	Α
Collector 电流 (脉冲)	ICP	受限于 Tjmax 的脉宽		72	А
二极管平均输出电流(Diode Average output current)	IO			10	А
允许功耗(Allowable Power Dissipation)	PD	Tc=25°C (我司理想的散热条件) *2		40	W
结温(Junction Temperature)	Тј			150	°C
储存温度(Storage Temperature)	Tstg			- 55 to +150	°C

• Diode t<sub>rr</sub>=70ns typ.

● 增强型 (Enhancement type)

注: \*1 Collector 电流由下式计算: Tjmax - Tc

 $I_{C}(Tc) = \frac{R_{th}(j-c) \times V_{CF}(sat) (I_{C}(Tc))}{R_{th}(j-c) \times V_{CF}(sat) (I_{C}(Tc))}$ 

\*2 我司的条件为背面散热。方法为:器件的背面涂上硅脂,然后将该器件贴在 铝制的水冷散热器上。

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### 电气特性 / Ta = 25°C (除非特殊指定)

参数	20	条件		值			苗店
	记号			min	typ	max	单位
集电极-发射极击穿电压 (Collector to Emitter Breakdown Voltage)	V(BR)CES	IC=500μA, VGE=0V		600			V
集电极-发射极截止电流	10.00		Tc=25°C			10	μA
(Collector to Emitter Cutoff Current)	ICES	ICES VCE=600V, VGE=0V				1	mA
栅极-发射极漏电流 (Gate to Emitter Leakage Current)	IGES	$V_{GE}=\pm 20V$ , $V_{CE}=0V$				±100	nA
栅极-发射极阈值电压 (Gate to Emitter threshold voltage)	V <sub>GE</sub> (off)	V <sub>CE</sub> =20V, I <sub>C</sub> =250µA		4.5		6.5	V
集电极-发射极饱和电压		at) VGE=15V, IC=10A	Tc=25°C		1.5	1.7	V
(Collector to Emitter Saturated Voltage)	VCE(sat)		Tc=125°C		1.7		V
正向二极管电压(Forward Diode Voltage)	VF	IF=10A			1.3		V
输入电容(Input Capacitance)	Cies	VCE =20V,f=1MHz			1440		pF
输出电容(Output Capacitance)	Coes				60		pF
反向传输电容(Reverse Transfer Capacitance)	Cres				30		pF

接下页



#### **ON Semiconductor®**

www.onsemi.cn

**TO-220F-3FS** 

### NGTB10N60FG

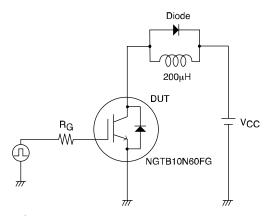
参数	记号     条件	友 (4	值			* /-
		min	typ	max	单位	
开启迟延时间(Turn-ON Delay Time)	t <sub>d</sub> (on)	$V_{CC}=300V,I_{C}=10A$ $R_{G}=30\Omega,L=200\mu H$ $V_{GE}=0V/15V$ $V_{clamp}=400V$ See Fig.1, See Fig.2		40		ns
上升时间(Rise Time)	tr			23		ns
开启时间(Turn-ON Time)	ton			110		ns
关断迟延时间(Turn-OFF Delay Time)	t <sub>d</sub> (off)			145		ns
下降时间(Fall Time)	tf			90		ns
关断时间(Turn-OFF Time)	toff			240		ns
总栅极电荷(Total Gate Charge)	Qg	- V <sub>CE</sub> =300V, V <sub>GE</sub> =15V, I <sub>C</sub> =10A		55		nC
栅极-发射极电荷(Gate to Emitter charge)	Qge			20		nC
栅极-集电极米勒电荷 (Gate to Collector "Miller" Charge)	Qgc			10		nC
二极管反向恢复时间 Diode Reverse Recovery Time)	t <sub>rr</sub>	I <sub>F</sub> =10A, di/dt=100A/µs, V <sub>CC</sub> =50V, See Fig.3		70		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

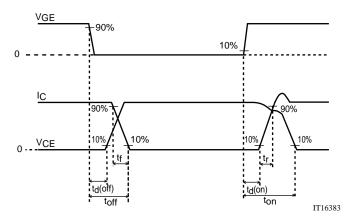
#### 热特性 / Ta = 25°C (除非特殊指定)

参数	记号	条件	值	单位
热阻 IGBT(结到外壳) Thermal Resistance IGBT (junction- Case)	Rth(j-c) (IGBT)	Tc=25℃ (我司的理想散热条件)*2	3.09	°C /W
热阻二极管(结到外壳) Thermal Resistance Diode (junction- Case)	Rth(j-c) (Diode)	Tc=25℃ (我司的理想散热条件)*2	4	°C /W
热阻(结到环境) Thermal Resistance (junction- ambient)	Rth(j-a)		59.5	°C /W

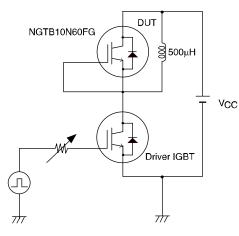
# 图 1: 开关时间测试电路

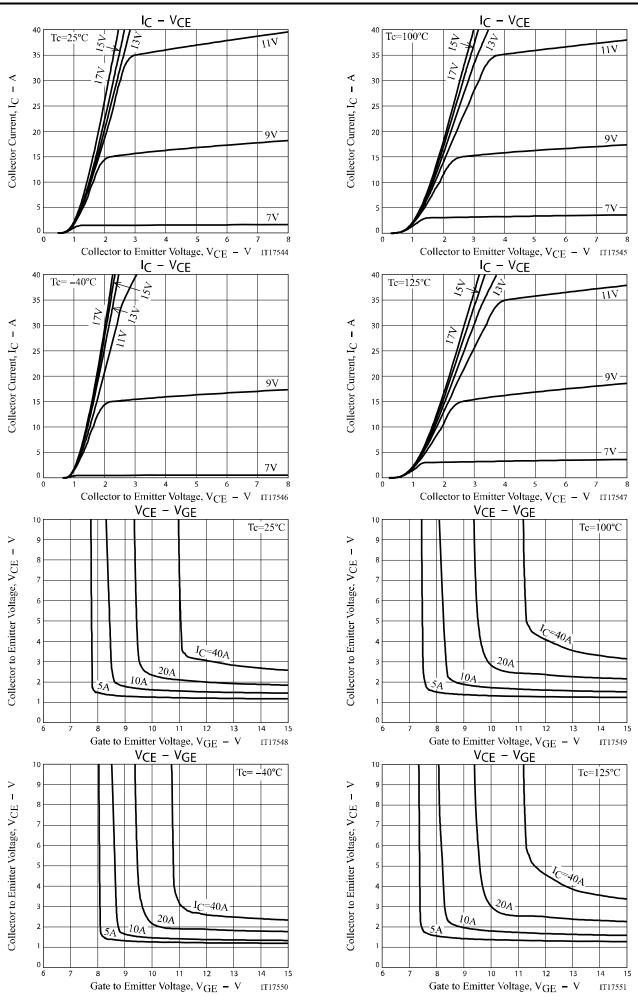


# 图 2:时间图

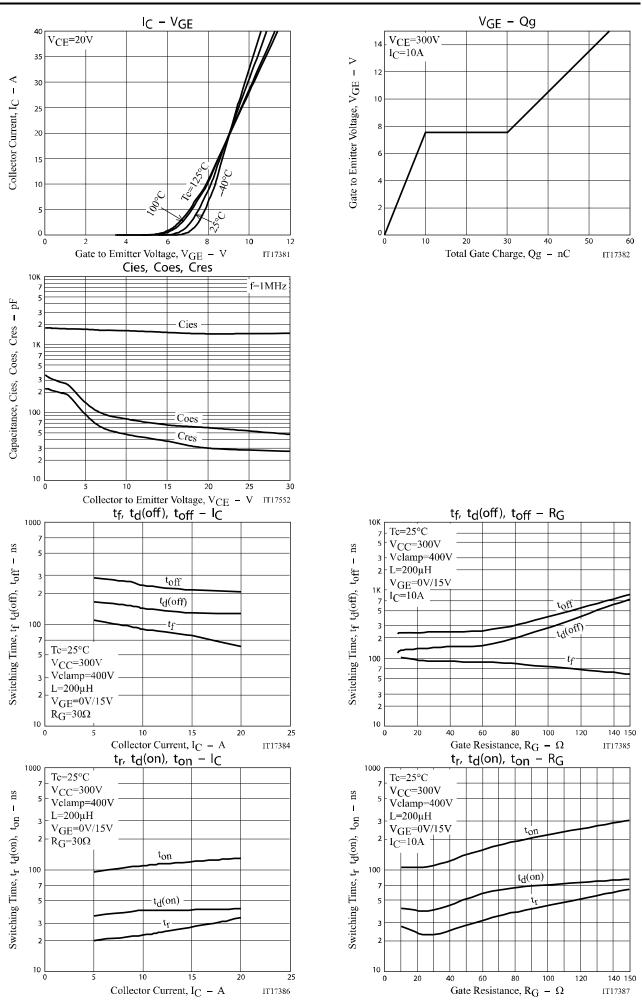


## 图 3:反向恢复时间测试电路



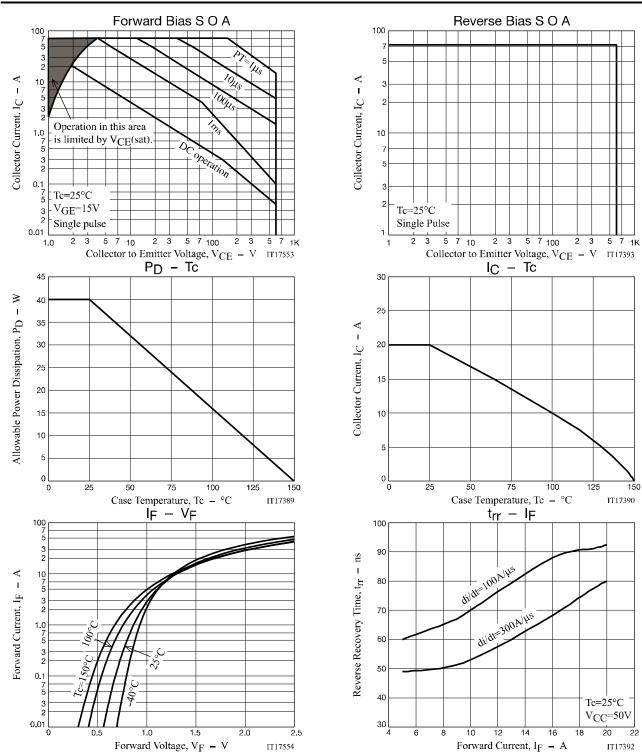


www.onsemi.cn 3



www.onsemi.cn 4

#### NGTB10N60FG



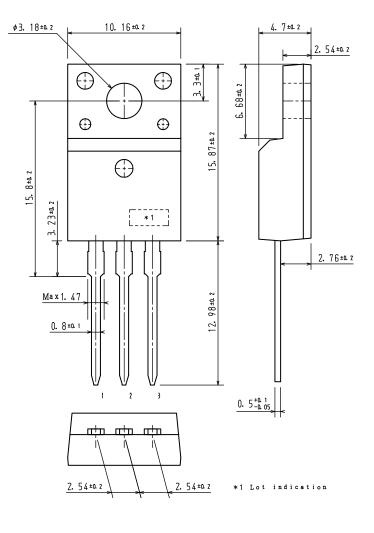
#### 封装尺寸

单位:mm

#### **TO-220F-3FS**

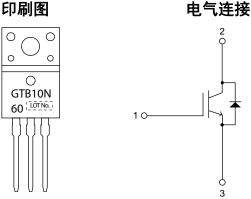
CASE 221AM **ISSUE O** 

- 1: Gate
- 2: Collector
- 3: Emitter



#### 订单与封装情报

Device	Package	Shipping	note
NGTB10N60FG	TO-220F-3FS SC-67	50 pcs. / tube	Pb-Free



3

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.